	_ 		·					R	EVIS	IONS										
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С	thi typ dev	rough pes l vices Ado	n 22. 19 an 3 21 1ed p	Ad d 20 and in 1	lded . A 22. ref	vend dded Cor	or Ca vend recta ce to	AGE (dor (ded e) de e) de) d	65786 CAGE rrors	type for 6177 to itlin	dev 2 fo Tabl	ice r e	9	93-04	4-28		М	. A.	Frye	2
REV																			Ι	
SHEET	ļ				ļ				ļ											
REV	C	С	С	С	С	С	С	С	С	С	С	С	С							
SHEET	15	16	17	18	19	20	21	22	23	24	25	26	27							
REV STAT				RE	V		С	С	C	С	С	С	С	С	С	С	С	A	С	С
					EET		1	2	3	4	5	6	7	8	9	10	11	12	13	14
PMIC N/A				PREP	ARED E	ames E.	. Jamis	son		DI	EFENS	SE EI						ΓER		
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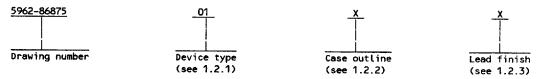
JUL 91

<u>DISTRIBUTION STATEMENT A</u>. Approved for public release; distribution is unlimited.

5962-E118-93

9004708 0005837 407 **1**

- 1. SCOPE
- 1.1 <u>Scope</u>. This drawing describes device requirements for class B microcircuits in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices".
 - 1.2 Part or Identifying Number (PIN). The complete PIN shall be as shown in the following example:



1.2.1 <u>Device types</u>. The device types shall identify the circuit function as follows:

Device type	Generic number 1/	Circuit function	Access time
01	11	K x 8 bit dual port CMOS SRAM (Master)	90 ns
02			70 ns
03			55 ns
04	11		45 ns
05			90 ns (data retention)
06		(x 8 bit dual port CMOS SRAM (Master)	
07	11		55 ns (data retention)
08			45 ns (data retention)
09			90 ns
10			70 ns
11			55 ns
12	 1k		45 ns
13			· · · · ·
14	14	C x 8 bit dual port CMOS SRAM (Stave)	90 ns (data retention)
15	16		
16	11	(x 8 bit dual port thus skan (stave)	55 ns (data retention)
17	31	(x 8 bit dual port CMOS SRAM (Slave)	
18	11		35 ns
19			35 ns
20			55 ns
	TK		55 ns
21		(x 8 bit dual port CMOS SRAM (Master)	55 ns (data retention)
22	1k	(x 8 bit dual port CMOS SRAM (Slave)	55 ns (data retention)

1.2.2 <u>Case outlines</u>. The case outlines shall be as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	<u>Terminals</u>	Package style
X	GDIP1-T48 or CDIP2-T48	48	dual-in-line
Y	See figure 1	48	square leadless chip carrier
Z	CQCC1-N52	52	square leadless chip carrier
U	See figure 1	48	flat pack

1.2.3 <u>Lead finish</u>. The lead finish shall be as specified in MIL-M-38510. Finish letter "X" shall not be marked on the microcircuit or its packaging. The "X" designation is for use in specifications when lead finishes A, B, and C are considered acceptable and interchangeable without preference.

1.3 Absolute maximum ratings. 2/

Supply voltage range (V _{CC})	-0.5 V dc to +7.0 V dc
Input voltage range	-0.5 V dc to +7.0 V dc
Output sink current	50 mA
Output short circuit duration	10 seconds
Power dissipation (Pp)	1.5 W

1/ Generic numbers are listed on the Standardized Military Drawing Source Approval Bulletin at the end of this document and will also be listed in MIL-BUL-103.

2/ All voltages referenced to GND.

STANDARDIZED MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER	SIZE A		5962-86875
DAYTON, OHIO 45444		REVISION LEVEL C	SHEET 2

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■ 9004708 0005838 343 **■**

Thermal resistance, junction-to-case $(\Theta_{\mbox{\scriptsize JC}})$: Case X -----30°C/W 3/ 12°C/W 3/ Case Y and U ------Case Z ---------------See MIL-STD-1835 Junction temperature ------+150°C 4/ Temperature under bias ------55°C to +125°C -65°C to +150°C Lead temperature (soldering, 10 seconds) -----+300°C 1.4 Recommended operating conditions. 5/ Supply voltage range (V_{CC}) -----4.5 V dc to 5.5 V dc Case operating temperature range (T_C) - - - - - - Minimum input high voltage level (V_{IH}) - - - - - Maximum input low voltage level (V_{IL}) - - - - - - --55°C to +125°C 2.2 V 0.8 V 2. APPLICABLE DOCUMENTS

2.1 Government specification, standard, and bulletin. Unless otherwise specified, the following specification, standard, and bulletin, of the issue listed in that issue of the Department of Defense Index of Specifications and Standards specified in the solicitation, form a part of this drawing to the extent specified herein.

SPECIFICATION

MILITARY

MIL-M-38510

- Microcircuits, General Specification for.

STANDARD

MILITARY

MIL-STD-883 MIL-STD-1835 Test Methods and Procedures for Microelectronics.
 Microcircuit Case Outlines.

BULLETIN

MILITARY

MIL-BUL-103

- List of Standardized Military Drawing (SMD's).

(Copies of the specification, standard, and bulletin required by manufacturers in connection with specific acquisition functions should be obtained from the contracting activity or as directed by the contracting activity.)

2.2 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing shall take precedence.

3. REQUIREMENTS

- 3.1 Item requirements. The individual item requirements shall be in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices" and as specified herein.
- 3.2 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-M-38510 and herein.
 - 3.2.1 <u>Case outlines</u>. The case outlines shall be in accordance with 1.2.2 herein and figure 1.
 - 3.2.2 <u>Terminal connections</u>. The terminal connections shall be as specified on figure 2.
 - 3.2.3 <u>Truth tables</u>. The truth tables shall be as specified on figure 3.
- 3/ When the thermal resistance for this case is specified in MIL-STD-1835, that value shall supersede the value indicated herein.
- 4/ Maximum junction temperature (T_J) may be increased to 175°C during the burn-in and steady state life test.

5/ All voltages referenced to GND.

STANDARDIZED MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER	SIZE A		5962-86875
		REVISION LEVEL C	SHEET 3

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- 3.2.4 Block diagram. The block diagram shall be as specified on figure 4.
- 3.2.5 <u>Die overcoat</u>. Polyimide and silicone coatings are allowable as an overcoat on the die for alpha particle protection only. Each coated microcircuit inspection lot (see inspection lot as defined in MIL-M-38510) shall be subjected to and pass the internal moisture content test at 5000 ppm (see method 1018 of MIL-STD-883). The frequency of the internal water vapor testing shall not be decreased unless approved by the preparing activity. Samples may be pulled any time after seal.
- 3.3 <u>Electrical performance characteristics</u>. Unless otherwise specified herein, the electrical performance characteristics are as specified in table I and apply over the full case operating temperature range.
- 3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are described in table I.
- 3.5 <u>Marking</u>. Marking shall be in accordance with MIL-STD-883 (see 3.1 herein). The part shall be marked with the part number listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked as listed in MIL-BUL-103 (see 6.6 herein).
- 3.6 <u>Certificate of compliance</u>. A certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-BUL-103 (see 6.6 herein). The certificate of compliance submitted to DESC-EC prior to listing as an approved source of supply shall affirm that the manufacturer's product meets the requirements of MIL-STD-883 (see 3.1 herein) and the requirements herein.
- 3.7 <u>Certificate of conformance</u>. A certificate of conformance as required in MIL-STD-883 (see 3.1 herein) shall be provided with each lot of microcircuits delivered to this drawing.
- 3.8 Notification of change. Notification of change to DESC-EC shall be required in accordance with MIL-STD-883 (see 3.1 herein).
- 3.9 <u>Verification and review</u>. DESC, DESC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.
 - 4. QUALITY ASSURANCE PROVISIONS
- 4.1 <u>Sampling and inspection</u>. Sampling and inspection procedures shall be in accordance with section 4 of MIL-M-38510 to the extent specified in MIL-STD-883 (see 3.1 herein).
- 4.2 <u>Screening</u>. Screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection. The following additional criteria shall apply:
 - a. Burn-in test, method 1015 of MIL-STD-883.
 - (1) Test condition C or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.
 - (2) $T_A = +125$ °C, minimum.
 - b. Interim and final electrical test parameters shall be as specified in table II herein, except interim electrical parameter tests prior to burn-in are optional at the discretion of the manufacturer.
- 4.3 <u>Quality conformance inspection</u>. Quality conformance inspection shall be in accordance with method 5005 of MIL-STD-883 including groups A, B, C, and D inspections. The following additional criteria shall apply.

STANDARDIZED MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444	SIZE A		5962-86875
	,	REVISION LEVEL C	SHEET 4

T4	0	Conditions 1/2/		Doutes	Limi		
Test	Symbol	-55°C ≤ T _C ≤ +125°C 4.5 V ≤ V _{CC} ≤ 5.5 V unless otherwise specified	Group A subgroups	Device type	Min	Max	Unii
High level output voltage	V _{ОН}	I _O = -4.0 mA, V _{IH} = 2.2 V, V _{IL} = 0.8 V	1, 2, 3	ALL	2.4	 	V
Low level output voltage (1/0 ₀ - 1/0 ₇ terminals only)	V _{OL} 1	I _O = 4.0 mA, V _{IH} = 2.2 V, V _{IL} = 0.8 V	1, 2, 3	ALL		0.4	 V
Low level open drain output voltage (BUSY _L , BUSY _R , INT _L , and INT _R terminals only)	V _{OL2}	I _O = 16 mA	1, 2, 3	All		0.5	V
High impedance output leakage current	Ioz	CE = V _{IH} , V _O = GND to V _{CC}	1, 2, 3	All	-10.0	10.0	μA
High level input voltage	v _{IH}		1, 2, 3	ALL	2.2		v
Low level input voltage	v _{IL}		1, 2, 3	All		0.8	V
Input leakage current	IIH	v _{IH} = 5.5 v	1, 2, 3	ALL		10.0	 μ
	IIL	V _{IL} = GND	1, 2, 3	ALL	-10.0		μΑ
Operating supply current (standby)	I _{SB1}	$ CE_L = CE_R \ge V_{IH}$, Both ports standby, $V_{CC} = 5.5 \text{ V}$	1, 2, 3	01-04, 09-12, 19-20		65	mA
				06-08, 14-16		55	
				05,13, 17,18		45	Ī
				21,22		60	ļ Ļ
	I _{SB2}	CEL or CER = VIH, one port standby, active port outputs	1, 2, 3	02-04, 10-12		135	 mA
		open, V _{CC} = 5.5 V		01,09, 19,20		125	
				06-08, 14-16		110	
				05,13, 17,18		100	
	1	!		21,22		T	T

See footnotes at end of table.

STANDARDIZED MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER	SIZE A		5962-86875
DAYTON, OHIO 45444		REVISION LEVEL C	SHEET 5

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	Symbol	Conditions $\underline{1}$ -55°C \leq T _C \leq +	<u>[/ 2/</u> 125°C Group	Group A	Device	Limi	ts	Unit
Operating summiv summer+	ļ	4.5 V \leq V _{CC} \leq sunless otherwise s	5.5 V	subgroups	type	Min	Max	-
Operating supply current (full standby)	I _{SB3}	$ \overline{CE}_L = \overline{CE}_B \ge V_{CC} - 0.2 $ $ V_{CC} = 5.5 \text{ V, } V_{IN} \le 0.2 $ $ V_{IN} \ge V_{CC} - 0.2 \text{ V, bot} $ $ ports full standby $	V, 2 V or th	1, 2, 3	01-04, 09-12, 17-20		30	mA
		ports full standby			05-08, 13-16, 21,22		10	
					21,22		140	
	I _{SB4}	$\overline{\text{CE}}_{\text{L}}$ or $\overline{\text{CE}}_{\text{R}} \geq \text{V}_{\text{CC}} - 0.2$ $ \text{V}_{\text{CC}} = 5.5 \text{ V, V}_{\text{IN}} \leq 0.2$ $ \text{V}_{\text{IN}} \geq \text{V}_{\text{CC}} - 0.2 \text{ V, one}$ full standby, active p	2 V,	1, 2, 3	04,12	<u> </u>	125	mA
		1ACC = 3.3 A AIN 7 0.5	vor		03,11		120	‡
	full standby	full standby, active r	ort		02,10	 	115	+
	İ	outputs open			19,20	İ	110	}
	ļ		j		08,16		95	İ
	ļ				07,15	ļ	90	Ţ
	ł				06,14		85	+
					17,18		1 80	
Operating supply current	Icc	CEL and CER = VIL, VCC = 5.5 V, f = 1 MHz		1, 2, 3	03,04,		230	mA
(dynamic)		$V_{CC} = 5.5 \text{ V}, \text{ f} = 1 \text{ MHz}$,		21,22	İ	<u>i</u>	<u> </u>
		both ports active	!		02,10	ļ	225	Ţ
					01,09	ļ	200	ļ
		ł	-		07,08 15,16	ļ	185	
	İ		i		06,14,		180	+
	İ	İ	į		19,20	i	100	1
	!	1	İ		05,13		160	1
					17,18		150	Ī
V _{CC} for data retention	v _{DR}	$ V_{CC} = 2.0 \text{ V}, \overline{CE} \ge V_{CC}$ $ V_{IN} \ge V_{CC} - 0.2 \text{ V or}$ $ V_{IN} \le 0.2 \text{ V}$	- 0.2 v,	1, 2, 3	05-08, 13-16, 21,22	 2.0 		V
Data retention current	ICCDR			1, 2, 3	05-08, 13-16, 21,22		4.0	mA
Chip deselect to data retention time 3/	tCDR	V _{CC} = 2.0 v, CE ≥ V _{CC} V _{IN} ≥ V _{CC} - 0.2 v or V _{IN} ≤ 0.2 v	- 0.2 v ,	1, 2, 3	 05-08, 13-16, 21,22	0	 	ns
			`					
Operation recovery time	t _R	V _{CC} = 2.0 V, CE ≥ V _{CC} V _{IN} ≥ V _{CC} - 0.2 V or V _{IN} ≤ 0.2 V	- 0.2 v,	1, 2, 3	05,13	90	<u> </u>	ns
<u>3</u> /	1	IN S OCE - U.S A OL	!		06,14	70	<u> </u>	Ļ
	1	IN 2 0.5 4			07,15	55 45		[
	i		}		08,16 21,22	35	l	Ļ

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T4	0	Conditions 1/	2/			Limits		
Test	Symbol	-55°C ≤ T _C ≤ +12 4.5 V ≤ V _{CC} ≤ 5. unless otherwise spe	25°C Grou .5 V subg ecified	p A roups	Device type	Min	Max	_ Unit
Input capacitance 4/5/	cIN	f = 1 MHz, $V_{IN} = V_{CC}$ or see 4.3.1c, $\frac{1}{1}_{A} = 25$ c		4	ALL		12	pF
Output capacitance	c _{out}	f = 1 MHz, V _{IN} = V _{CC} or see 4.3.1c, T _A = 25 c	GND	4	01-20		10	pF
Functional tests		See 4.3.1d	7.8	A, 8B	All		''	
Read cycle		4	1.2.5	.,		· · · · · · · · · · · · · · · · · · ·		<u> </u>
Read cycle time	tavav	6/	9, 10,	0. 11	17-22	35	Ţ	
•	AVAV			-,	04,08	45	1	ns
					12,16 01,05	90	+	†
					09,13	70		+
					10,14	<u>i</u>	<u> </u>	<u> </u>
					03,07 11,15	55	-	
Address access time	tAVQV	6/	9. 1	0, 11	 <u>17-22</u>		35	ļ
	AVQV	2'	''	o,	04,08	<u>† </u>	45	ns
					12,16 01,05	 	90	+
			İ		09,13	<u> </u>		↓
			i		02,06 10,14		70	
	ļ		į		03,07	!	55	†
· · · · · · · · · · · · · · · · · · ·	-				11,15	 	-	
Output hold from address	^t AXQX	<u>6</u> /	9, 1	0, 11	17,18	3	<u> </u>	ļ
change			i		01,05	10		ns
					02-04,	0		1
					10-12,		İ	
					14-16 <i>,</i> 19-22			
Output enable access	 t _{oLQV}	<u>6</u> /	9, 1	0, 11	17,18		15	
time			İ	•	01,02,		40	ns
					05,06, 09,10,	1		
					13,14 03,07,		35	1
					111,15	ļ		1
	1				04,08, 12,16		30	
			Ì		21,22		25	Ţ
The state of the s			L		19,20	1	20	
See footnotes at end of ta	able.						•	
	DARDIZ		SIZE				5	962-86
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							. ~	

Test		Conditions 1/	<u>2</u> /		Limits		T
	Symbol	$-55^{\circ}C \le T_C \le +12$ $4.5 V \le V_{CC} \le 5.$ unless otherwise spe	5°C Group A 5 V subgroups cified	Device type	Min	Max	Unit
Read cycle							<u> </u>
3/7/ Output enable to output active	t _{OELZ}	<u>6</u> /	9, 10, 11	All	3		ns
Output enable high to high Z <u>3/ 7/ 8</u> /	t _{OEHZ}	 <u>6</u> /	9, 10, 11	 17,18, 21,22		15	
				01,05,		40	ns
	į			02,06, 10,14		35	Ī
				03,07,		30	†
				04,08,		1	
				12,16, 19,20	<u> </u>	20	<u></u>
3/ 7/ Chip enable to output active	† CELZ	<u>6</u> /	9, 10, 11	All	5		ns
Chip enable high to high Z <u>3</u> / <u>7</u> / <u>8</u> /	t _{CEHZ}	<u>6</u> /	9, 10, 11	17,18, 21,22		15	
	j			01,05,		40	ns
				02,06,		35	†
				10,14 03,07,	 	30	+
				11,15 04,08,	<u> </u>	<u> </u>	+
				12,16,		20	
hip enable to output	t _{ELQV}	<u>6</u> /	9, 10, 11	17-22		35	<u> </u>
valid			-	04,08 12,16		45	ns
			į	01,05 09,13		90	
				02,06	l·	70	†
				10,14 03,07	55	55	1
The state of the s		Control of the second of the second		11,15		 	
hip enable low to <u>3</u> / power up	^t PU	<u>6</u> /	9, 10, 11	ALL	0		ns
hip enable high to <u>3</u> / power down	t _{PD}	<u>6</u> /	9, 10, 11	ALL	! 	50	ns

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Tank	S	Conditions 1/	2/			Limits	
Test	Symbol 	-55° C \leq T _C \leq +1 4.5 V \leq V _{CC} \leq 5 unless otherwise sp	25°C Group .5 V subgro ecified			n M	Unit ax
Write cycle							
Write recovery time		<u>6</u> /	0.40	14 104 3			
with the recovery time	twhax	<u>0</u> /	9, 10, 	11 <u>01-2</u> 21,2		2	ns
Chip enable to		41	0 10	00 107 0	2 7		
end-of-write	t _{ELWH}	<u>6</u> /	9, 10, 	11 <u>17-2</u> 01,0			ns
				09,1	3	İ	
	-			02,0 10,1		ן כ	
				03,0	7, 40)	
				11,1 04,0	5 8, 3:	-	
	_ii	· · · · · · · · · · · · · · · · · · ·		12,1			
Address setup time		<u>6</u> /	9, 10,	11 01-2	0		-
	tAVWL	<u> </u>		21,2	2 (5	ns
Write pulse width	t	6/	9, 10,	11 17 1	8 3	, [
	twLwH	±′	[7 , 10,	11 <u>17,1</u> 04,0			ns ns
				12,1	6		
			}	01,0	5, 60 3	'	
			İ	02,0	6, 50)	
				10,1 03,0		<u> </u>	
			ļ	11,1	5		
	<u> </u>			21,2 19,2			<u>-</u> <u> </u>
Data valid to		41	0.40				
end-of-write	t _{DVWH}	<u>6</u> /	9, 10,	11 <u>17-2</u> 04,0			 ns
			ļ	12,1	6		
				01,0 09,1	5, 40 3)	
			į	02,0	6, 30)	
				10,1 03,0	7.		
			į	11,1	5, 20)	
	++			21,2	5		
Write enabled to output	t _{WLQZ}	<u>6</u> /	9, 10,				15
in high impedance state <u>3</u> / <u>7</u> / <u>8</u> /				21,2 04,0			20 ns
<u> </u>				12,1	6,		20 ns
				19,2 01,0	D		40
				09,1	3	İ	İ
				02,0 10,1	6,		35
				03,0	7,		30
See footnotes at end of t	able.			[11,1	- I		
	STANDARDIZED		SIZE			Т	5962-8
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Test	Data nold time		4.5 V ≤ V _{CC} ≤ 5.5 V	Group A subgroups	1000.00	·		Unit
### Pack of time twhDX 6/ 9, 10, 11 ALL 0 ns	Data nold time		ancess officiwise specified	subgroups	type	Min	Max	
Section Sect								<u></u>
End-of-write to data active Address valid to end-of-write \$\frac{1}{4}\text{VHQX}\$ \$\frac{6}{2}\text{ P, 10, 11 } All 0		tWHDX	<u>6</u> /	9, 10, 11	ALL	0		ns
Address match to BUSY state Table	ind-of-write to data	twHQX	<u>6</u> /	9, 10, 11	ALL	0		ns
BUSY timing Address match to BUSY state		tavwh	<u>6</u> /	9, 10, 11	 <u>17-22</u>	30		
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	end-or-write				01,05,	85		ns
11,15					02,06,	50		1
04,08, 35 12,16 35 12,16 35 12,16 35 12,16 35 12,16 35 12,16 35 12,16 35 12,16 35 12,16 35 15 15 15 15 15 15 15					03,07,	40		Ť
Address match to BUSY state table					04,08,	35	1	ţ
State SAA SP SP SP SP SP SP S	USY timing				112,10	L		<u> </u>
1 1 1 1 1 1 1 1 1 1		t _{RAA}	6/ 9/	9, 10, 11	17.19		20	<u> </u>
thip enable to BUSY state tbac 6/9/ state p, 10, 11 17,19 20 10,05 45 10,07, 30 10,05 45 10,07, 35 10,07, 35 10,07, 35 10,07, 35 10,07, 35 10,05, 45 10,05, 45 10,05, 45 10,05, 45 10,05, 45 10,05, 45 10,05, 45 10,05, 45 10,05, 45 10,07, 35 10,05, 45 10,05, 45 10,05, 45 10,05, 45 10,06,07	state				04,08,			ns
thip enable to BUSY state tbac delta beta beta beta beta beta beta beta be					01-03,			†
state BAC 17, 19 20 04,08, 21 30 01,05 45 02,03, 35 06,07, 17,19 20 17,19 20 21 30 21 30 21 30 21 30 21 30 21 30 21 30 21 30 21 30 21 30 21 30 20 21 30 21 30 20 21 30 21 30 20 21 30 20 21 30 21 30 20 21 30 21 30 20 21 30 20 21 30 21 30 20 21 30 21 30 20 21 30 21 30 20 21 30 20 21 30 21 30 20 21 30 21 30 20 21 30 21 30 20 21 30 20 21 30 21 30 20 30 30 30 30 30 30 30	hin anable to Buoy	†			05-07		45	_
21 30 01,05 45 02,03, 35 06,07,		^t BAC	<u>6</u> / <u>9</u> /	9, 10, 11			20_	Ļ
101,05 45 02,03, 35 06,07,							30	ns
ddress no match to not BUSY state t _{BDA} 6/9/ 9, 10, 11 17,19 20 21 30 04,08, 35 07,05, 45 02,03, 40 06,07								†
ddres <u>s no</u> match to not BUSY state t _{BDA} 6/9/ 9, 10, 11 17,19 20 21 30 04,08, 35 01,05, 45 02,03, 40 06,07		!!		ļ			35	Ī
not BUSY state 21 30 04,08, 35 ns 01,05, 45 02,03, 40 06,07		 			06,07,		<u> </u>	
21 30	ddres <u>s no</u> match to	tena	6/ 9/	9. 10. 11	17 10		20	i I
04,08, 35 ns 01,05, 45 02,03, 40 06,07	not BUSY state	500		, , , , , ,	21			-
01,05, 45 02,03, 40 06,07		1 1		İ	04,08,			ns
06,07				ļ				
		1		ļ			40	
ee footnotes at end of table.		l			06,07		l	
	ee footnotes at end of tab	le.						

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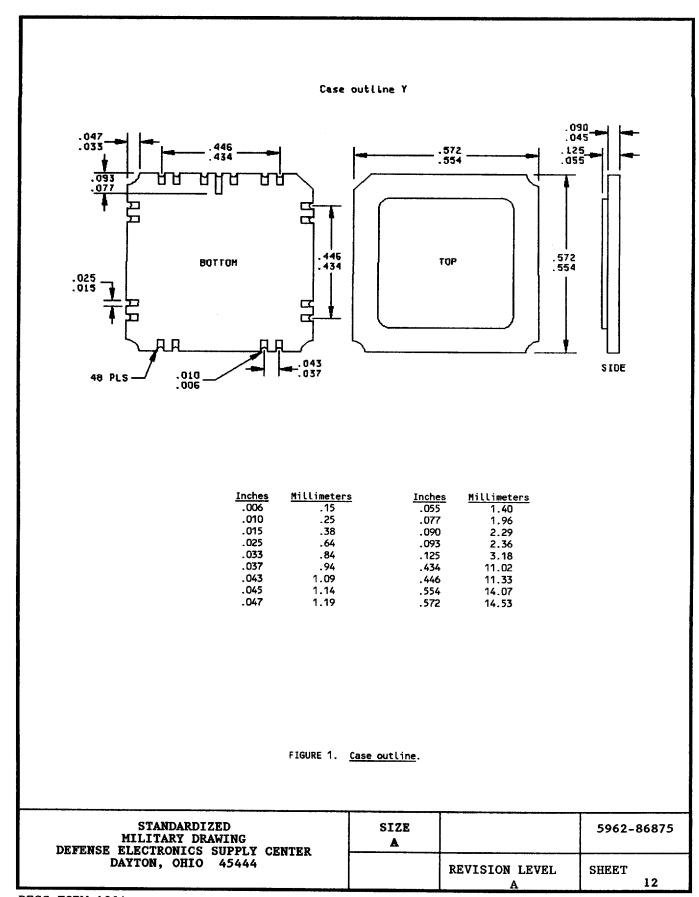
SIZE A		5962-86875
	REVISION LEVEL C	SHEET 10

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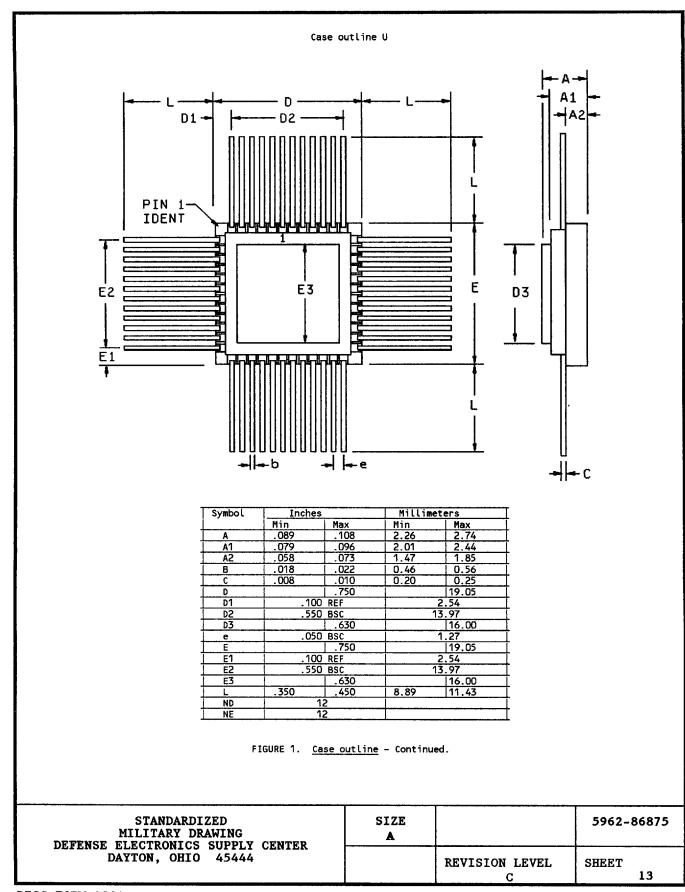
Test	Symbol	Conditions <u>1</u> / -55°C ≤ T _C ≤ +1	25°C Group	A	Device	Limi	ts	Unit
		4.5 V ≤ V _{CC} ≤ 5	.5 V subgr	oups	type	Min	Max	į
BUSY timing	1	unless otherwise sp	ecified			<u> </u>	J	<u> </u>
<u> </u>					т	Г		
Chip disable to not BUSY	t _{BDC}	<u>6</u> / <u>9</u> /	9, 10	, 11	17,19	<u> </u>	20	!
state					04,08,		25	ns
					01,05	<u> </u>	25 45	
					02,03,			Ī
	+				06,07,		30	-
Address arbitration priority setup time	^t APS	<u>6</u> / <u>9</u> /	9, 10	, 11	01-08,	5	İ	ns
priority secup time			}		17,19, 21	 		
nterrupt timing						L		
					1	l	T	
nterrupt setup time	t INS	<u>6</u> / <u>9</u> / <u>10</u> /	9, 10,	, 11	17-20 21,22	<u> </u>	25 35	1
					04,08,	1	40	l ns
					12,16		<u> </u>	1
					01,05,		55	
					02,06, 10,14		50	Ī L
	į į				03,07,		45	
	+	····			11,15		ļ	<u> </u>
nterrupt reset time	tINR	<u>6</u> / <u>9</u> / <u>10</u> /	9, 10,	. 11	17,18		15	!
					04,08		40	ns
					12,16 01,05		55	L
					09,13 02,06		<u> </u>	Ĺ
					10,14		50	
					03,07 11,15		45	
					21,22		35	Ĺ
/ All voltages reference	and to CND	. Negative undershoot			19,20		25	<u> </u>
/ May not be tested, bu / Effective capacitance meter. / Tested only initially / A pull-up resistor to otherwise I SB will ex / Transition is measure / Switching times test / Switching times test / The left port interru left port reads from	ut shall be calculat and afte over on t ceed valued ±500 mV circuit a circuit a circuit s set 3fE. The	e guaranteed to the li ed from C = ΔQ/ΔV with r a <u>ny</u> design changes. he CE input is required	mits specified in	table V _{CC} = ce de	I. 5.0 V, o	r measure during V ₍ ce figure	ed with	capacit
	DARDIZE	ING	SIZE A				59	62-86
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						C. V C. I .		

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Device	T		Device	T	
types	, A	ll	types	A	ιι
Case	х,		Case	Х,	
outlines	Y, and U	Z	outlines	Y, and U	Z
Terminal		· · · · · · · · · · · · · · · · · · ·	Terminal		<u> </u>
number	Terminal	symbol	number	Terminal	symbol
1	CEL	CEL	27	1/0 _{2R}	I/O _{OR}
2	R/WL	R/W _L	28	1/0 _{3R}	1/0 _{1R}
3	BUSY	BUSY	29	1/0 _{4R}	1/0 _{2R}
4	INT	INTL	30	1/0 _{5R}	1/0 _{3R}
5	ŌĒL	NC	31	1/0 _{6R}	1/0 _{4R}
j 6	AOL	OE _L	32	1/0 _{7R}	1/0 _{5R}
7	1 ^1	l A _{∩t}	33	I Aop	1 170
8	^2ı	^11	34	MAD	I/07R
9	^ 3 1	1 ^A 21	35	1 ^7D	110
10	^ <u>4</u> 1	וציין	36	*AP	A _{9R}
11	^A 51	1 AZI	37	1 ASD	Ago
12	^6I	1 751	38	740	1 77D
13	^7!	l *6ı	39	MZD	AAD
14	^Q	וליי	40	^2p	Λς,ρ
15	A ₉ L	' ^8i	41	1 A18	MAD GAM
16	AOL 1/O _{OL}	^9L	42	A _{OR}	A _{3R}
17	1/0 _{1L}	1/0 _{0L}	43	OE _R	A _{2R}
18	1/0 _{2L}	1/0 _{1L}	44	INTR	A _{1R}
19	1/0 _{3L}	1/0 _{2L}	45	BUSYR	A _{OR}
20	1/0 _{4L}	1/0 _{3L}	46	R/W _R	OE _R
21	1/0 _{5L}	1/0 _{4L}	47	CER	NC
22	1/0 _{6L}	1/0 _{5L}	48	v _{cc}	INTR
23	1/0 _{7L}	^{1/0} 6L	49		BUSYR
24	GND	1/0 _{7L}	50		R/W _R
25	I/O _{OR}	NC	51	i i	CER
26	I/O _{1R}	GND	52		v _{cc} K
l					

NOTE: An "L" suffix on a terminal indicates it applies to the "left" port, an "R" indicates it applies to the "right" port.

FIGURE 2. <u>Terminal connections</u>.

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	Flags <u>2</u> /		uts	port inp	Right	Left port inputs			
Function	BUSYR	BUSY	OE _R	CER	R/W _R	ŌĒL	CEL	R/W _L	
Left port in power down mode.	Н	н	x	X	X	x	H	х	
Right port in power down mode.	Н	н	х	Н	X	X	х	х	
Data on left port written in memory	н	н	x	X	X	x	L	L	
Data in memory output on left mode.	н	Н	х	х	x	L	 L	Н	
Data on right port written in memory	н	н	X	L	L	x	х	х	
Data in memory output on right port	Н	н	L	L	Н	x	х	x	

Interrupt flag control 1/

	Left port						Right po		Function	
R/W _L	CEL	OEL	AO _L -A9 _L	INT	R/WR	CER	ŌER	AO _R -A9 _R	INTR	1
L	 L 	x	3FF	x	x	x	х	x	L	Set right INT _R flag.
х	 X 	 x 	x	X	 н 	L	L	3FF	 н 	Reset right INT _R flag.
х	X	x	x	 L 	L	L	X	3FE	X	Set left INT _L flag.
Н	 L 	x	3FE	 H	X	x	X	X	X	Reset left INT _L flag.

See footnotes at end of figure.

FIGURE 3. <u>Truth table</u>.

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						_		
CE	arbitration	with	address	match	before	CE	1/	3/

	Left port			Right port Flags 4/			i		 Function	
R/W _L	CEL	OEL	AO _L -A9 _L	R/W _R	CER	OE _R	AO _R -A9 _R	BUSYL	BUSYR	
X	LBR	X	MÁTCH	X	L	X	MATCH	 H	Ŀ	Left operation permitted. Right operation not permitted.
х	 L 	X	MATCH	x	LBL	X	MATCH	L	н	Left operation not permitted. Right operation permitted.
x	LST	X	MATCH	X	LST	X	MATCH	Н	L	 Arbitration resolved.
х	LST	X	MÁTCH	х	LST	X	MATCH	L	Н	Arbitration resolved.

Address arbitration with $\overline{\text{CE}}$ low before address match $\underline{1}/\underline{5}/\underline{6}/$

Left port				Right port			Flags <u>2</u> /		 Function	
R/W _L	CEL	ŌĒ	A0 _L -A9 _L	R/W _R	CER	OE _R	AO _R -A9 _R	BUSYL	BUSYR	T
x	L	x	YBR	x	L	X	VALID	 H 	L	 Left operation permitted. Right operation not permitted.
x	L	x	VALID	X	L	х	 VBL	L	H	Left operation not permitted. Right operation permitted.
X	L	X	VST	x	 L	х	VST	 	 L	 Arbitration resolved.
х	E	X	VST	X	L	х	VST	L	H	Arbitration resolved.

X = don't care, H = logic 1 state, L = logic 0 state, LST = left and right, $\overline{CE} = low$ within 5 ns of each other.

FIGURE 3. <u>Truth table</u> - Continued.

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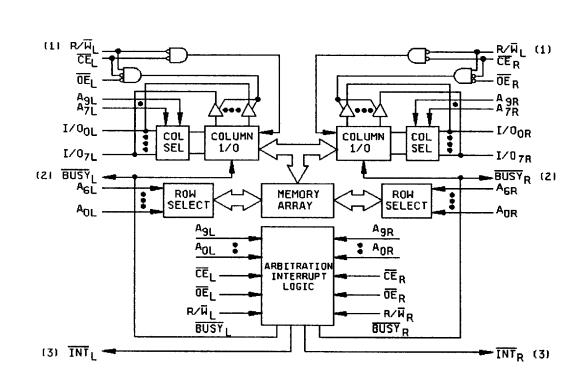
INT flags = Logic DON'T CARE state.

LBR = left CE = low \geq 5 ns before right CE. LBL = right CE = low \geq 5 ns before left GE.

AO_L - AO_L \neq AO_R - A9_R.

VST = left and right addresses match within 5 ns of each other. VBR = left addresses valid \geq 5 ns before right address.

 $[\]underline{6}$ / VBL = right address valid ≥ 5 ns before left address.



NOTES:

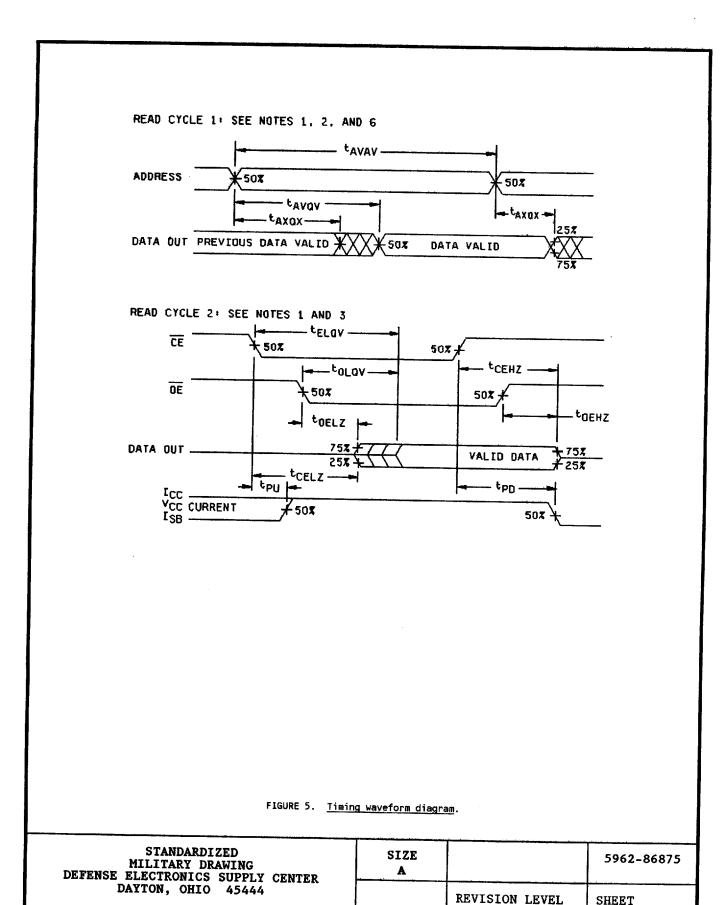
- An "L" suffix on a terminal indicates it applies to the "left" port, an "R" indicates it applies to the "right" port.
- These signals are outputs on device types 01 through 08, 17, 19 and 21 and inputs on device types 09 through 16, 18, 20, and 22. On device types 01 through 08, 17, 19, and 21 these signals are open drain and require pull-up resistors.
- 3. Open drain outputs: Pull-up resistor required.

FIGURE 4. Block diagram.

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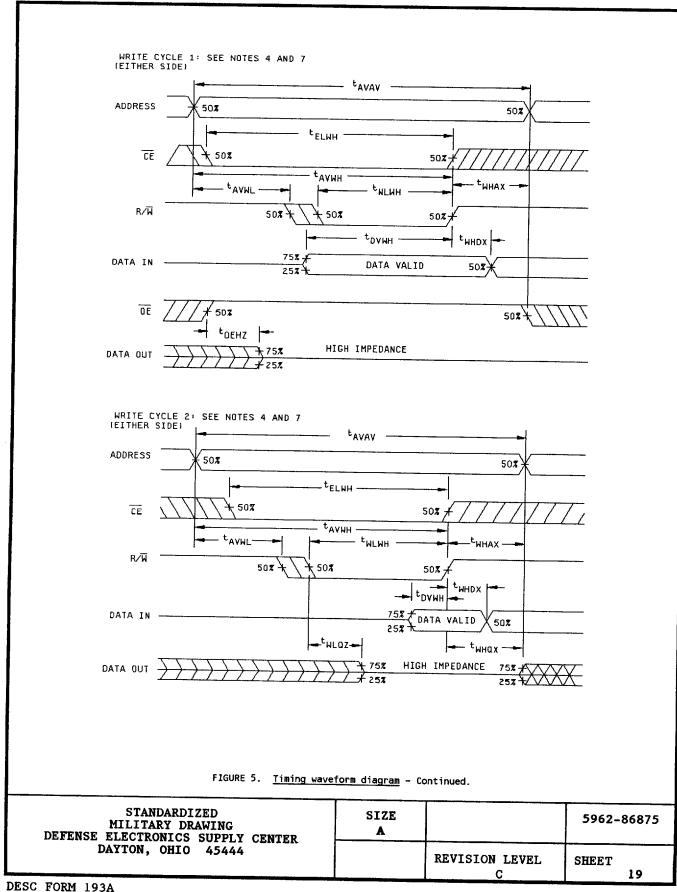
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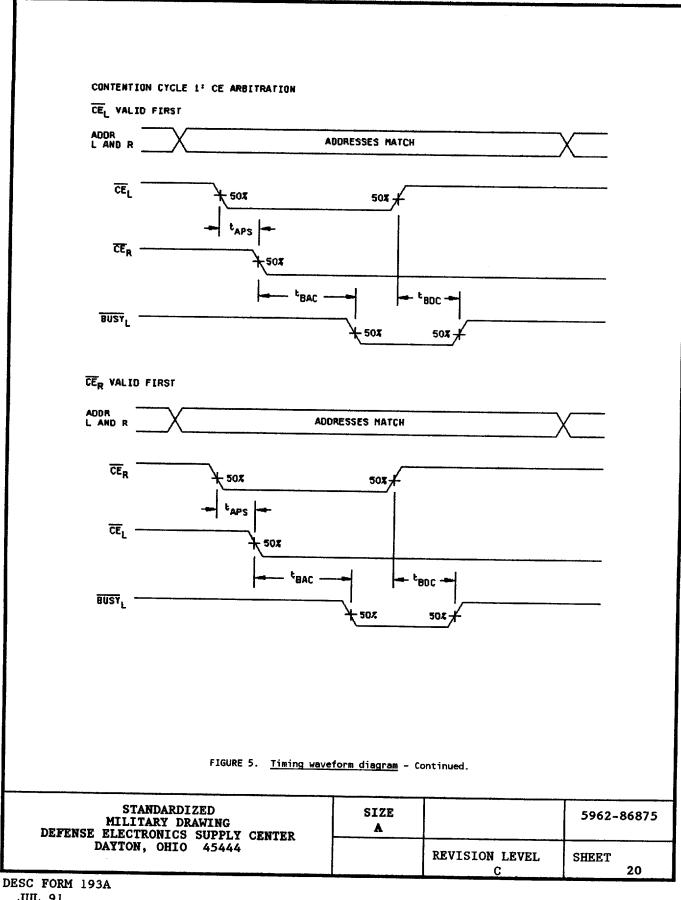


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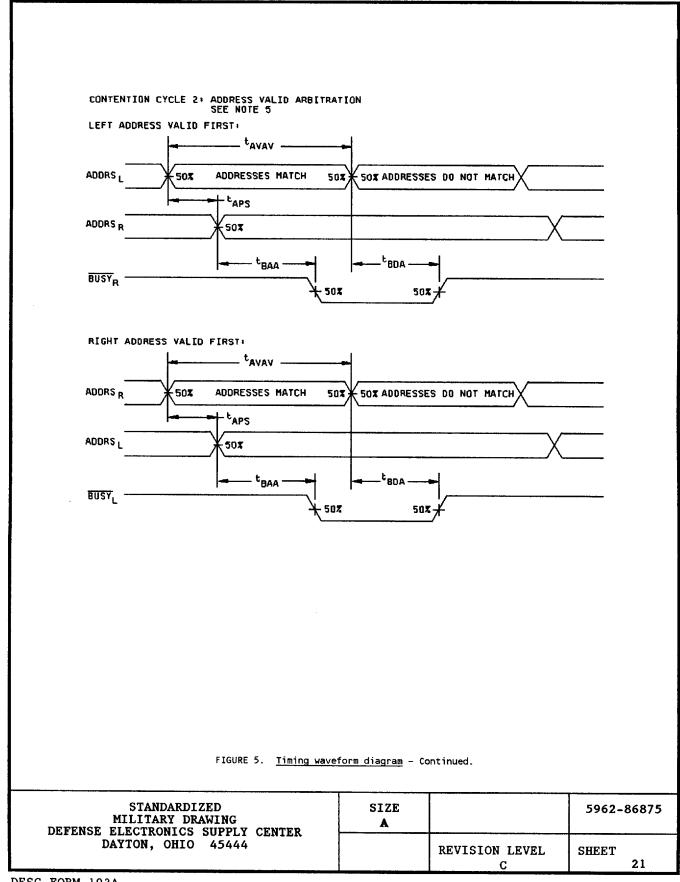
18

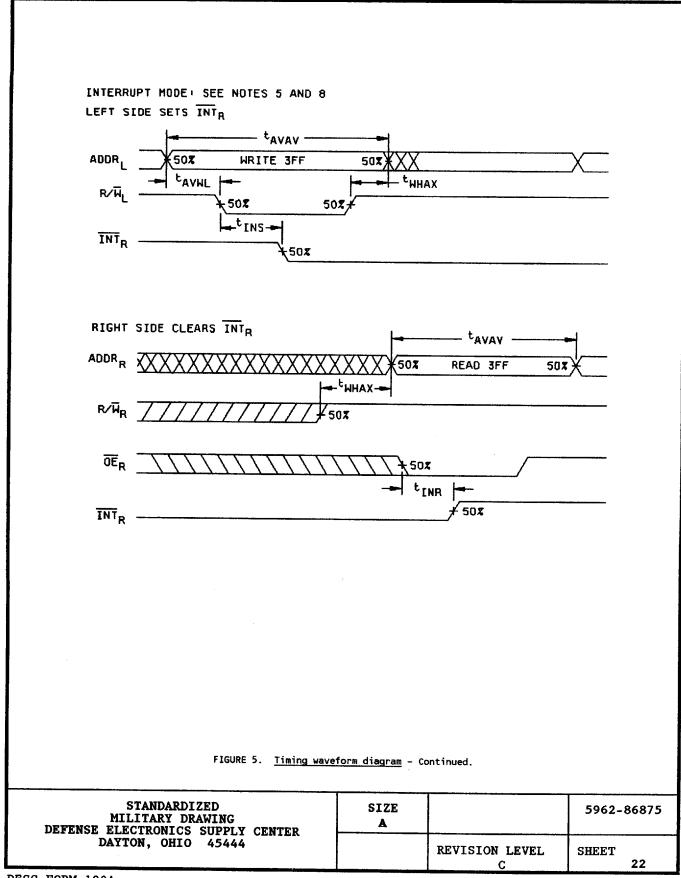


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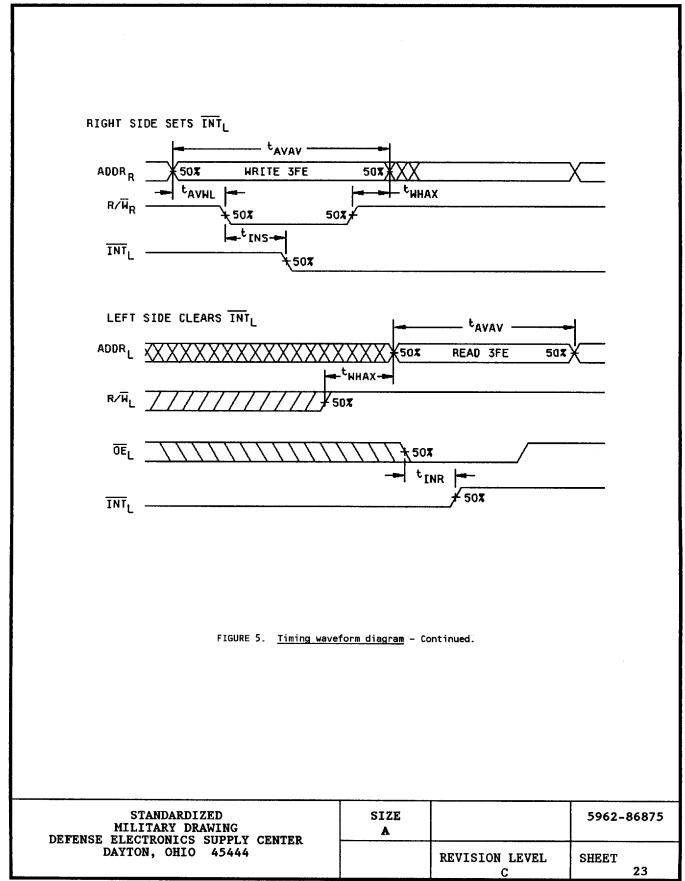


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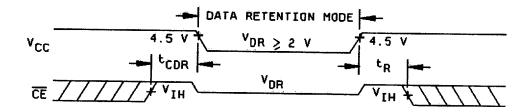


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DATA RETENTION WAVEFORM



NOTES:

- 1. R/W is high (logic 1 state) for read cycles.
- 2. Device is continuously enabled, $CE = V_{11}$.

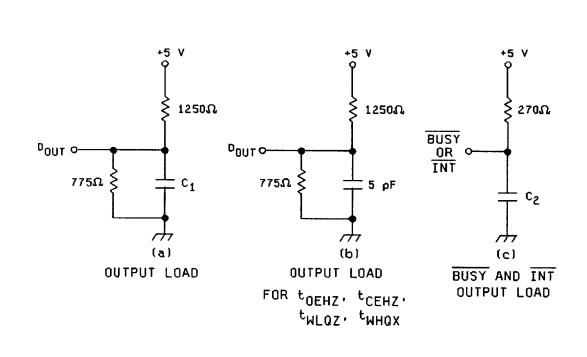
 3. Address valid prior to or coincident with CE transition low (logic O state).
- 4. If CE goes high (logic 1 state) simultaneously with R/W high 1.1 cc goes high (togic 1 state) simultaneously with R/W high (Logic 1 state), the outputs remain in the high impedance state.
 5. <u>CE</u>_L = CE_R = V_{IL}.
 6. OE = V_{IL}.
 7. <u>R/W</u> = V_{IH} during the address transition.
 8. INT_R and INT_L are reset high (togic 1 state) during power up.

FIGURE 5. Timing waveform diagram - Continued.

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NOTES:

- Tolerances on resistors and capacitors = ±10 percent.
 Input pulse levels are at GND to 3.0 V.
- 3. Input rise/fall times are at 5 ns.
- Input timing reference levels are at 1.5 V.
 Output reference levels are at 1.5 V.
- 6. c_1 and c_2 capacitance loads will be 100 pF for all devices, except for device types 04, 08, 12, and 16-22 which will be at 30 pF.

FIGURE 6. Switching times test circuit.

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TABLE II. Electrical test requirements. 1/

MIL-STD-883 test requirements	Subgroups (per method 5005, table I)		
Interim electrical parameters (method 5004)			
Final electrical test parameters (method 5004)	1*,2,3,7,8A, 8B,9,10,11		
Group A test requirements (method 5005)	1,2,3,4,7,8A, 8B,9,10,11		
Groups C and D end-point electrical parameters (method 5005)	2,3,7,8A,8B		

^{1/} Any or all subgroups may be combined when using high speed testers.
* PDA applies to subgroup 1.

4.3.1 Group A inspection.

- a. Tests shall be as specified in table II herein.
- b. Subgroups 5 and 6 in table I, method 5005 of MIL-STD-883 shall be omitted.
- c. Subgroup 4 (C_{IN} and C_{OUT} measurement) shall be measured only for the initial test and after process or design changes which may affect capacitance. Sample size is fifteen with zero accept and all input and output terminals tested.
- d. Subgroups 7 and 8 shall include verification of the truth table.
- 4.3.2 Groups C and D inspections.
 - a. End-point electrical parameters shall be as specified in table II herein.
 - b. Steady-state life test conditions, method 1005 of MIL-STD-883.
 - (1) Test condition C or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.
 - (2) $T_A = +125$ °C, minimum.
 - (3) Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.
- 5. PACKAGING
- 5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-M-38510.
- 6. NOTES
- 6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use when military specifications do not exist and qualified military devices that will perform the required function are not available for original equipment manufacturer application. When a military specification exists and the product covered by this drawing has been qualified for listing on QPL-38510, the device specified herein will be inactivated and will not be used for new design. The QPL-38510 product shall be the preferred item for all applications.

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- 6.2 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.
- 6.3 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-481 using DD Form 1693, Engineering Change Proposal (Short Form).
- 6.4 <u>Record of users</u>. Military and industrial users shall inform Defense Electronics Supply Center when a system application requires configuration control and the applicable SMD. DESC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronics devices (FSC 5962) should contact DESC-EC, telephone (513) 296-6047.
- 6.5 <u>Comments</u>. Comments on this drawing should be directed to DESC-EC, Dayton, Ohio 45444, or telephone 513-296-5377.
- 6.6 <u>Approved sources of supply</u>. Approved sources of supply are listed herein. Additional sources will be added to MIL-BUL-103 as they become available. The vendors listed in MIL-BUL-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to DESC-EC.

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